

General Description

The WSR10N65F is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR10N65F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

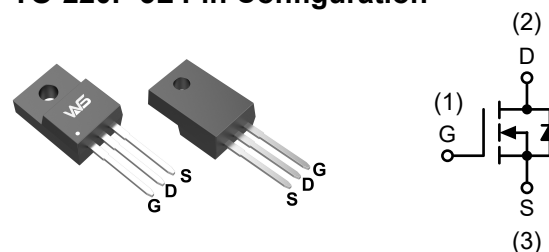
Product Summary

BV_{DSS}	R_{DS(on)}	I_D
650V	600mΩ	10A

Applications

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply(UPS)
- Adapter.

TO-220F-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	650	V
V _{GS}	Gate-Source Voltage	±30	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	10	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	6	A
I _{DM}	Pulsed Drain Current ^{1,2,5}	40	A
EAS	Single Pulse Avalanche Energy ¹	900	mJ
P _D	Total Power Dissipation ^{1,5}	39	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	3.2	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	650	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =250uA	---	0.6	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =3.5A	---	600	800	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.57	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =650V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =520V, V _{GS} =0V, T _J =55°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±30V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =40V, I _D =3.5A	---	5	---	S
Q _g	Total Gate Charge (10V)	V _{DD} =520V, V _{GS} =10V, I _D =10A	---	21	---	nC
Q _{gs}	Gate-Source Charge		---	7.5	---	
Q _{gd}	Gate-Drain Charge		---	6	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =300V, V _{GS} =10V, I _D =10A, R _G =25Ω	---	28	---	ns
T _r	Rise Time		---	70	---	
T _{d(off)}	Turn-Off Delay Time		---	35	---	
T _f	Fall Time		---	53	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	1120	---	pF
C _{oss}	Output Capacitance		---	130	---	
C _{rss}	Reverse Transfer Capacitance		---	4.9	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,2,5}	V _G =V _D =0V, Force Current	---	---	10	A
I _{SM}	Pulsed Source Current ^{1,2}		---	---	40	A
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V, I _S =10A, T _J =25°C	---	---	1.4	V
t _{rr}	Reverse Recovery Time	I _F =10A, dI/dt=40A/μs, T _J =25°C	---	491	---	nS
Q _{rr}	Reverse Recovery Charge		---	2296	---	nC

Notes:

Note 1 : limited by maximum junction temperature.

Note 2 : Bond wire current limit.

Note 3 : V_{DS}=520V, I_D=10A.

Note 4 : I_D=0.5A, V_{DD}=50V, T_J=25°C.

Note 5 : Repetitive Rating : Pulse width limited by maximum junction temperature.

Typical Characteristics

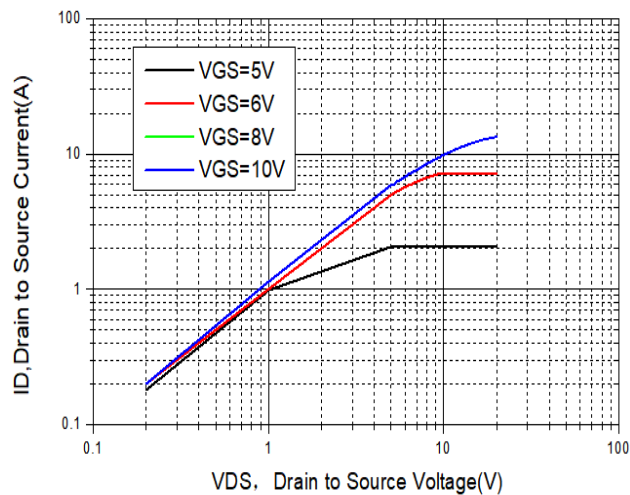


Figure 1 Output Characteristics

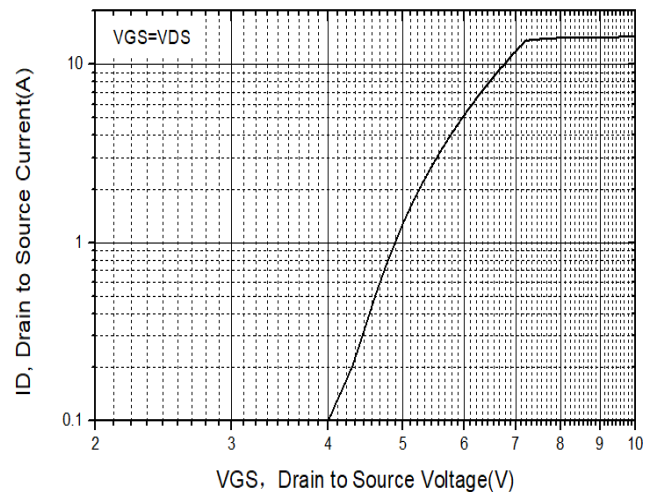


Figure 3 $R_{DS(on)}$ - I_D Characteristics

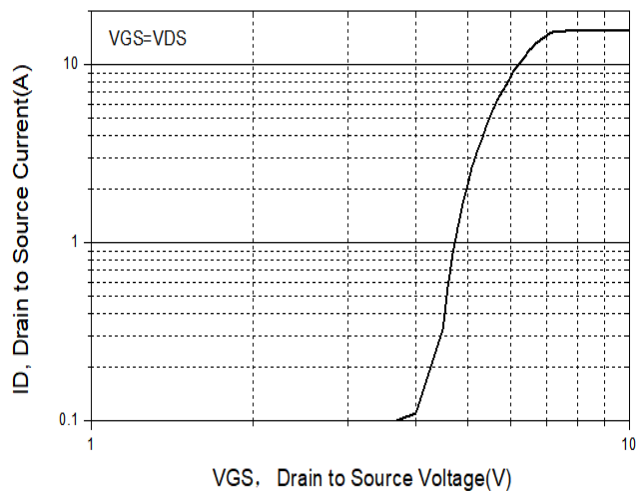


Figure 2 Transfer Characteristics

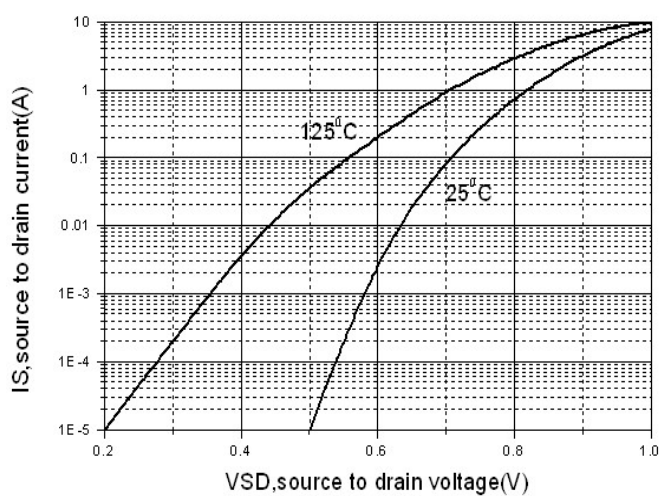


Figure 4 Body diode Characteristics

Typical Characteristics

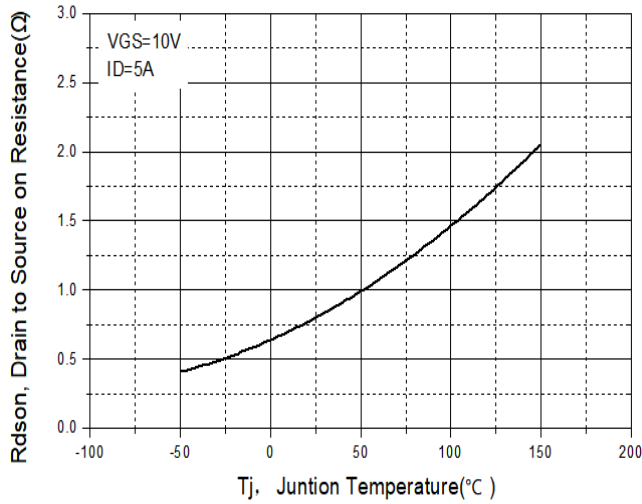


Figure 5 Rdson- Tj Relation

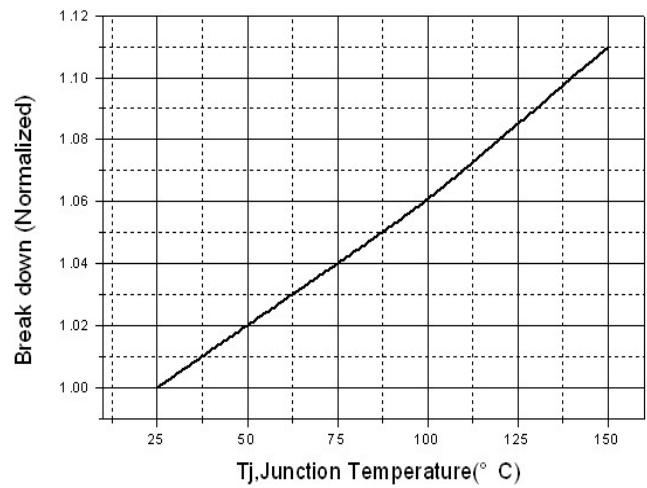


Figure 6 BVDSS vs Junction Temperature

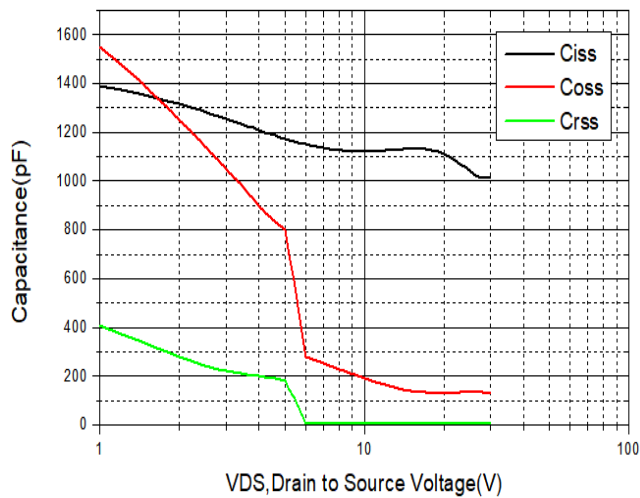


Figure 7 Capacitance vs Vds

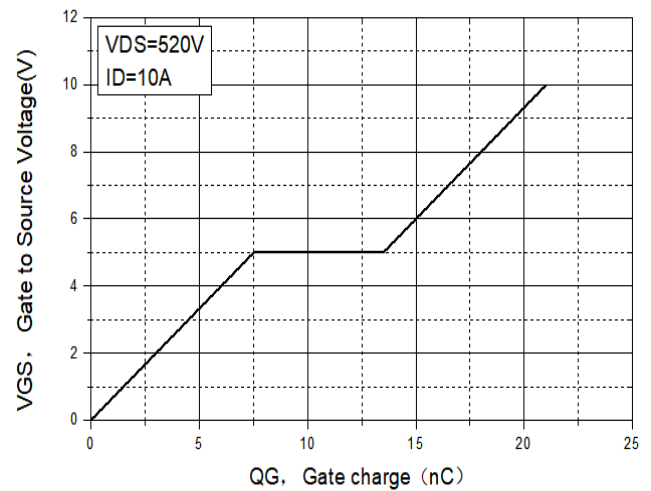


Figure 8 VGS vs QG Characteristics

Typical Characteristics

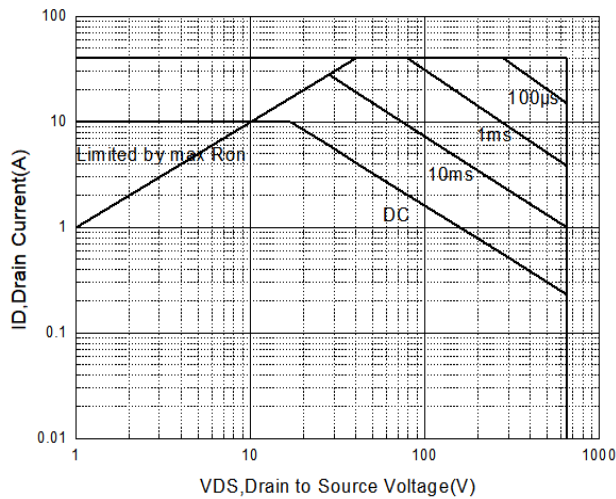


Figure 9 Safe Operation Area

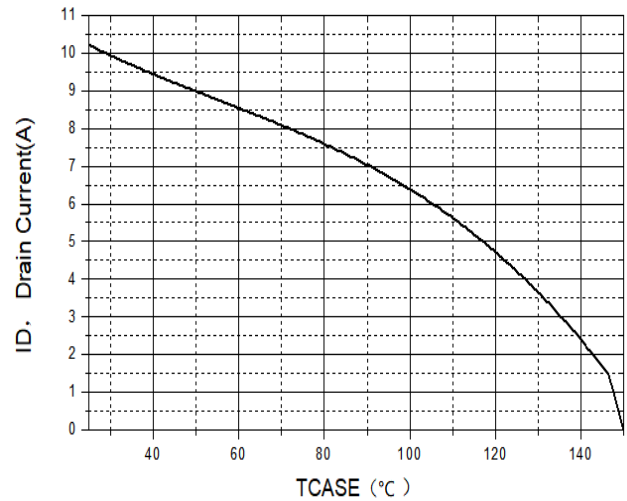


Figure 10 Maximum current attenuation

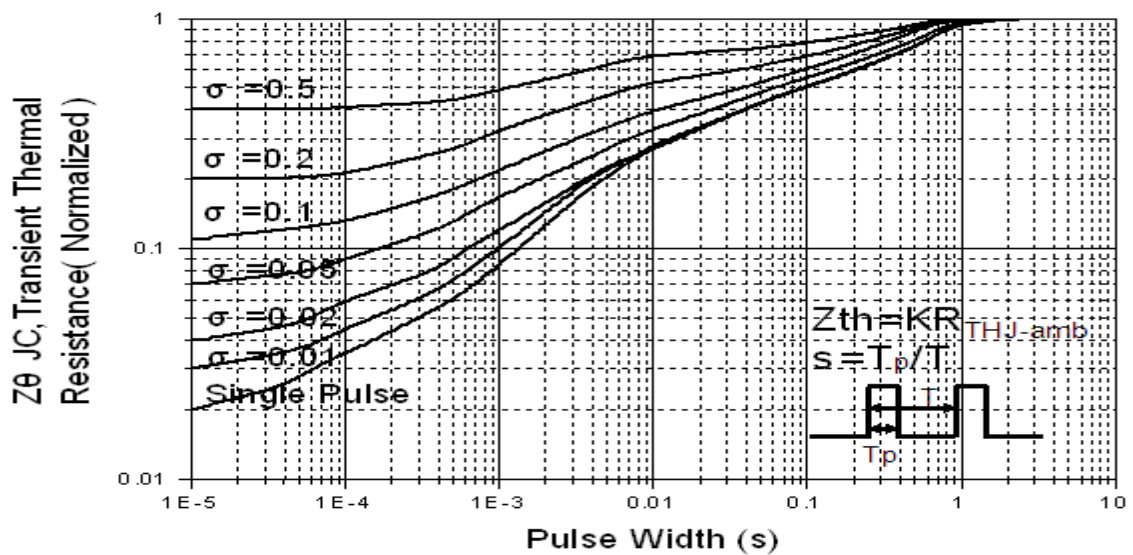
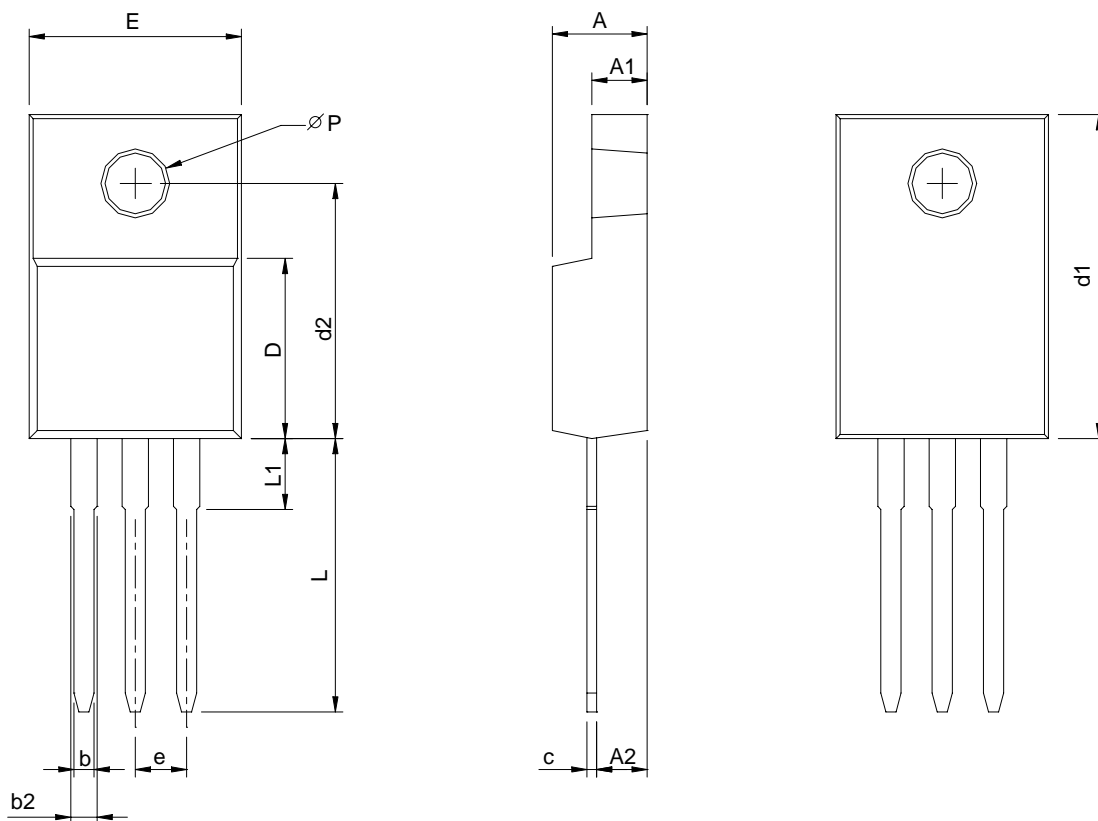


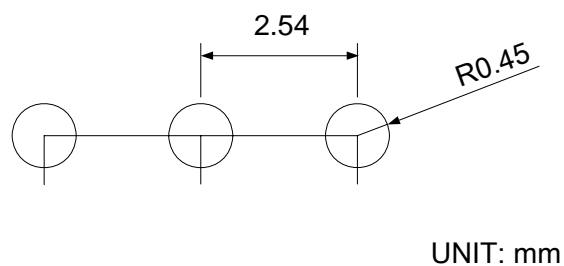
Figure 11 Normalized Maximum Transient Thermal Impedance

Packaging information



SYMBOL	TO-220F-3L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.20	4.80	0.165	0.189
A1	2.34	3.20	0.092	0.126
A2	2.10	2.90	0.083	0.114
b	0.50	0.90	0.020	0.035
b2	0.91	1.90	0.035	0.075
c	0.30	0.80	0.012	0.031
D	8.10	9.40	0.319	0.370
d1	14.50	16.50	0.571	0.650
d2	12.10	12.90	0.476	0.508
E	9.70	10.70	0.382	0.421
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.570
L1	1.60	4.00	0.063	0.157
P	3.00	3.60	0.118	0.142

RECOMMENDED LAND PATTERN



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